Alfa-MOS Technology

AFN6872S

150V N-Channel Enhancement Mode MOSFET

General Description

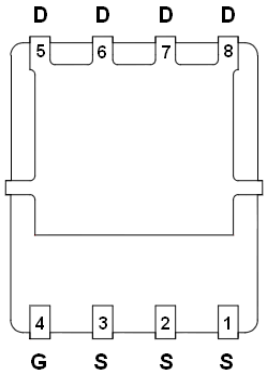
AFN6872S, N-Channel enhancement mode MOSFET, uses Advanced Trench Technology to provide excellent $R_{DS(ON)}$, low gate charge.

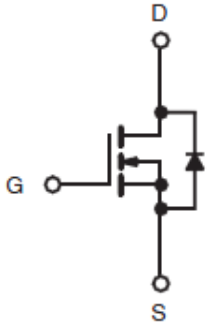
These devices are particularly suited for low voltage power management, and low in-line power loss are needed in commercial industrial surface mount applications.

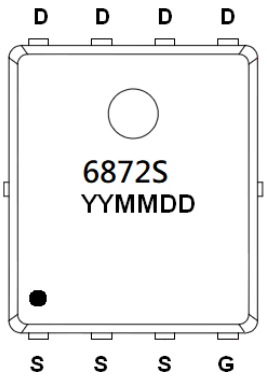
Features

- I_D=20A,$R_{DS(ON)}$=18mΩ@V_{GS}=10V
- I_D=15A,$R_{DS(ON)}$=20mΩ@V_{GS}=6V
- Super high density cell design for extremely low $R_{DS\ (ON)}$
- DFN5X6-8L package design

Pin Description (DFN5X6-8L)







Application

- Networking / Telecom / Server
- LED Lighting Applications
- Quick Charger Applications
- DC-DC Primary Side Switch

Pin Define

Pin	Symbol	Description
1~3	S	Source
4	G	Gate
5~8	D	Drain

Ordering Information

Part Ordering No.	Part Marking	Package	Unit	Quantity
AFN6872SFN568RG	6872S	DFN5X6-8L	Tape & Reel	2500 EA

※ 6872S : Parts Code
※ YYMMDD : Date Code
※ AFN6872SFN568RG : 13”Tape & Reel ; Pb- Free ; Halogen –Free

Absolute Maximum Ratings

(T_A=25℃ Unless otherwise noted)

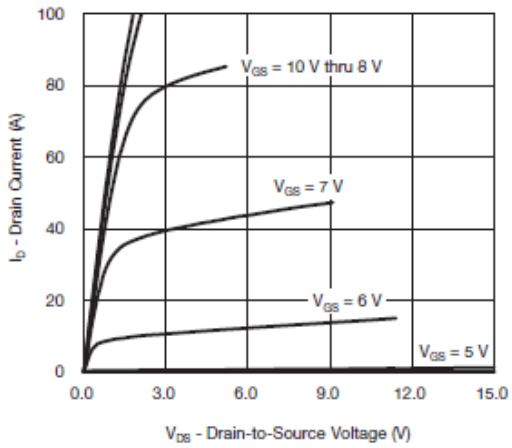
Parameter			Symbol	Typical		Unit
Drain-Source Voltage			V_{DSS}	150		V
Gate –Source Voltage			V_{GSS}	±25		V
Continuous Drain Current(T_J=150℃)	T_C=25℃	T_C=70℃	I_{DSM}	54	43	A
	T_A=25℃	T_A=70℃		13	10	
Pulsed Drain Current (t=100us)			I_{DM}	100		
Continuous Source Current(Diode Conduction)	T_C=25℃		I_S	60		
	T_A=25℃			5.6		
Single Pulse Avalanche Current	L=0.1mH		I_{AS}	30		
			E_{AS}	45		mJ
Power Dissipation	T_C=25℃	T_C=75℃	P_D	104	66	W
	T_A=25℃	T_A=75℃		6.25	4.0	
Operating Junction Temperature			T_J	150		℃
Storage Temperature Range			T_{STG}	-55/150		℃
Maximum Junction-to-Ambient	t ≤ 10 s		$R_{\theta JA}$	20		℃/W
Maximum Junction-to-Case (Drain)	Steady-State		$R_{\theta JA}$	1.2		

Electrical Characteristics

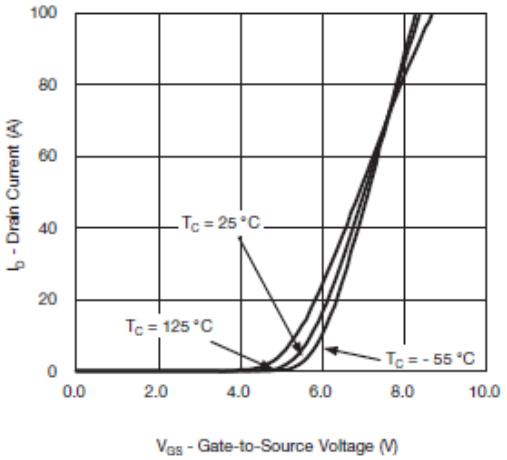
(T_A=25℃ Unless otherwise noted)

Parameter	Symbol	Conditions	Min.	Typ	Max.	Unit
Static						
Drain-Source Breakdown Voltage	$V_{(BR)DSS}$	V_{GS}=0V,I_D=250uA	150			V
Gate Threshold Voltage	$V_{GS(th)}$	V_{DS}=V_{GS},I_D=250uA	2.0	3.0	4.0	
Gate Leakage Current	I_{GSS}	V_{DS}=0V,V_{GS}=±25V			±100	nA
Zero Gate Voltage Drain Current	I_{DSS}	V_{DS}=120V,V_{GS}=0V			1	uA
		V_{DS}=120,V_{GS}=0V T_J=85℃			30	
On-State Drain Current	$I_{D(on)}$	V_{DS}≧10V,V_{GS}=10V	40			A
Drain-Source On-Resistance	$R_{DS(on)}$	V_{GS}=10V,I_D=20A		13	18	mΩ
		V_{GS}=6V,I_D=15A		15	20	
Forward Transconductance	g_{FS}	V_{DS}=10,I_D=20A		30		S
Diode Forward Voltage	V_{SD}	I_S=8A,V_{GS}=0V		0.75	1.3	V
Dynamic						
Total Gate Charge	Q_g	V_{DS}=75V,V_{GS}=7.5V I_D≡20A		24	40	nC
Gate-Source Charge	Q_{gs}			8		
Gate-Drain Charge	Q_{gd}			10		
Gate Resistance	R_g	f=1MHz	0.3	1.0	2.0	Ω
Input Capacitance	C_{iss}	V_{DS}=75V,V_{GS}=0V f=1MHz		1300		pF
Output Capacitance	C_{oss}			350		
Reverse Transfer Capacitance	C_{rss}			30		
Turn-On Time	$t_{d(on)}$	V_{DD}=75V,R_L=3.75Ω I_D≡20A,V_{GEN}=10V R_G=1Ω		10	20	ns
	t_r			12	24	
Turn-Off Time	$t_{d(off)}$			15	30	
	t_f			7	14	

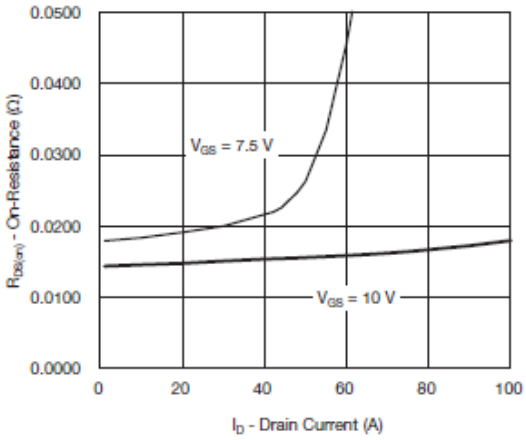
Typical Characteristics



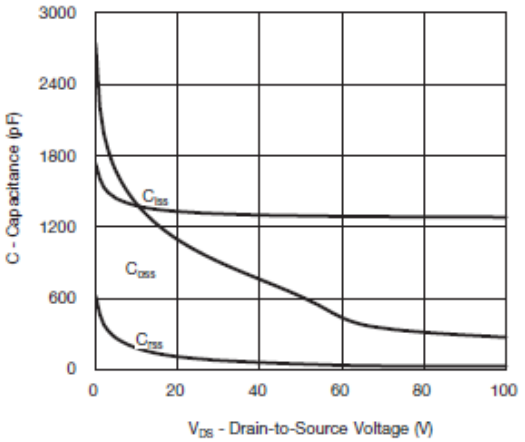
Output Characteristics



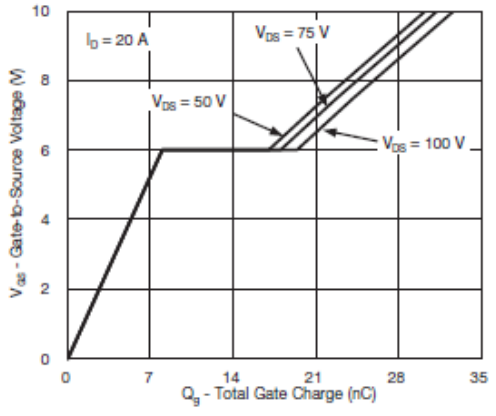
Transfer Characteristics



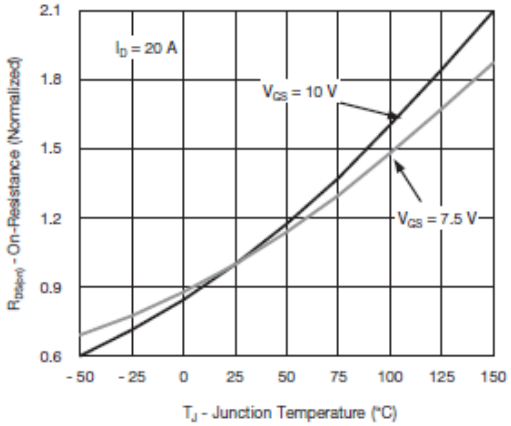
On-Resistance vs. Drain Current



Capacitance

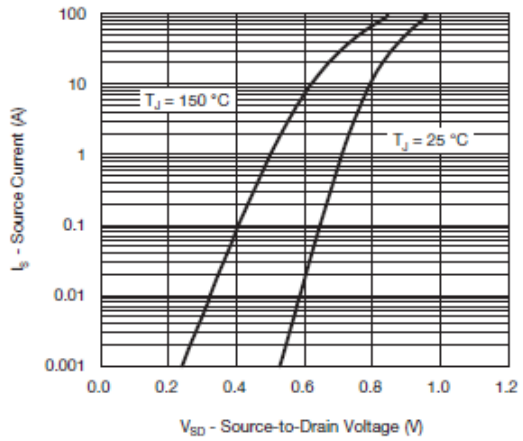


Gate Charge

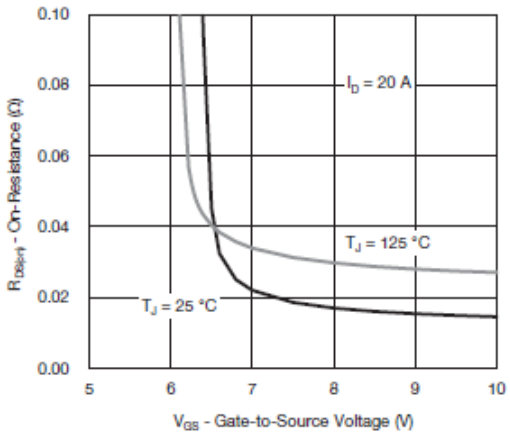


On-Resistance vs. Junction Temperature

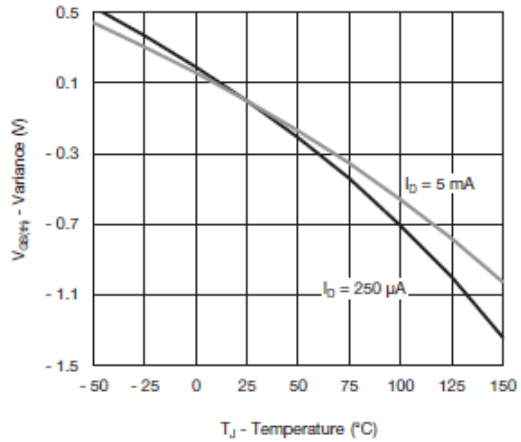
Typical Characteristics



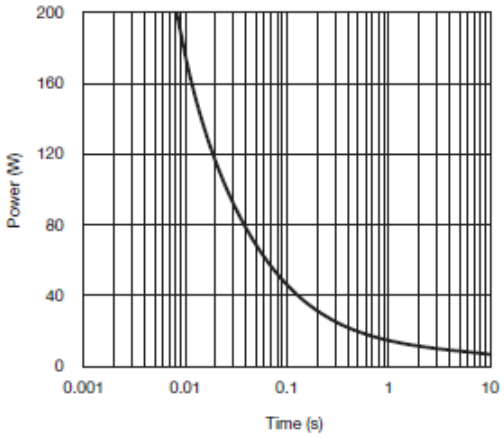
Source-Drain Diode Forward Voltage



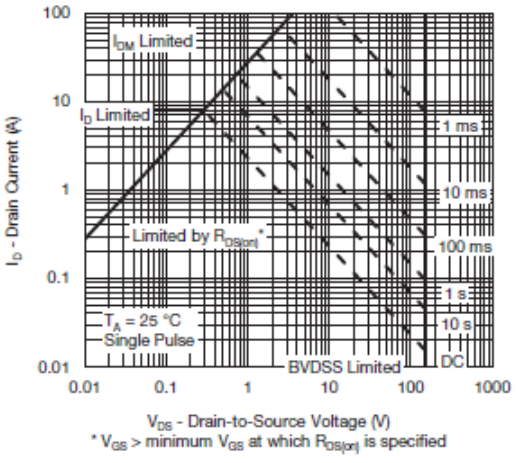
On-Resistance vs. Gate-to-Source Voltage



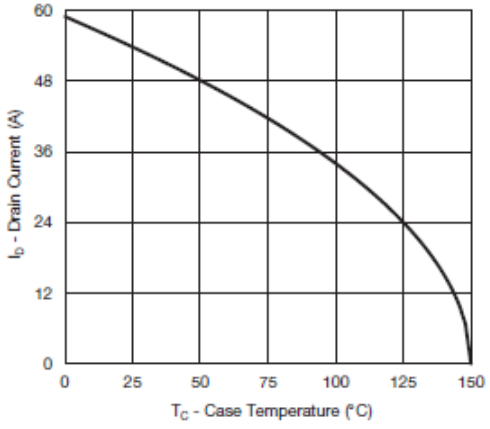
Threshold Voltage



Single Pulse Power, Junction-to-Ambient

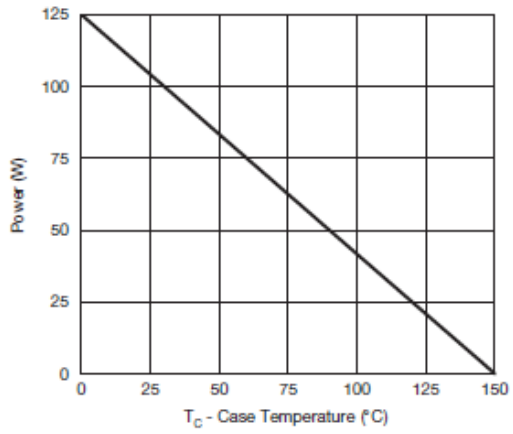


Safe Operating Area, Junction-to-Ambient

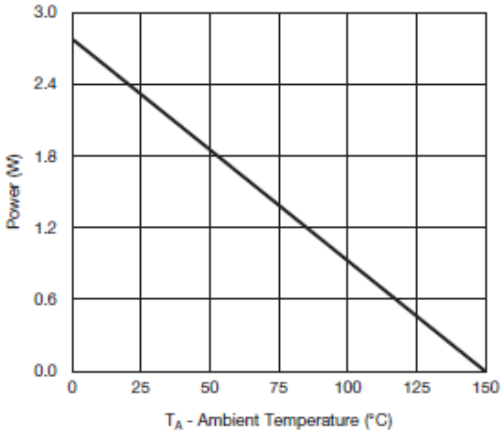


Current Derating*

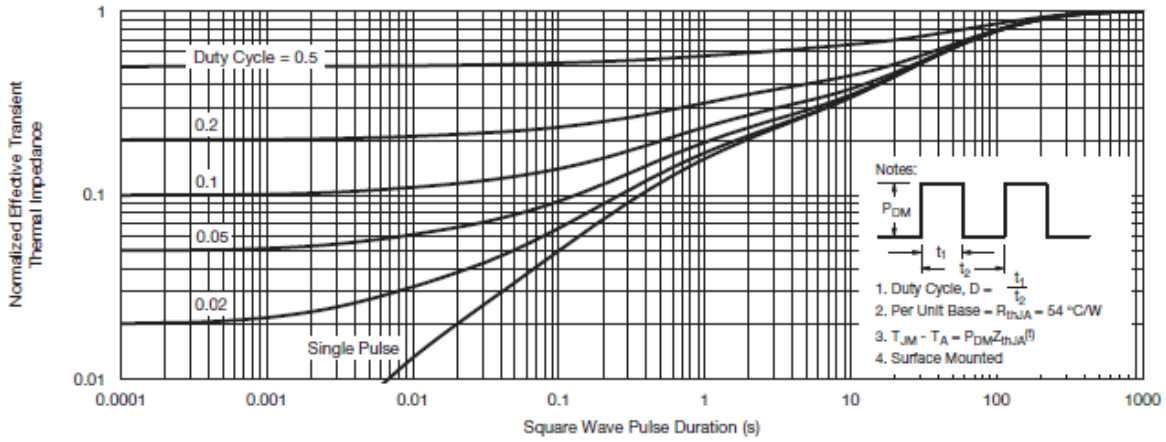
Typical Characteristics



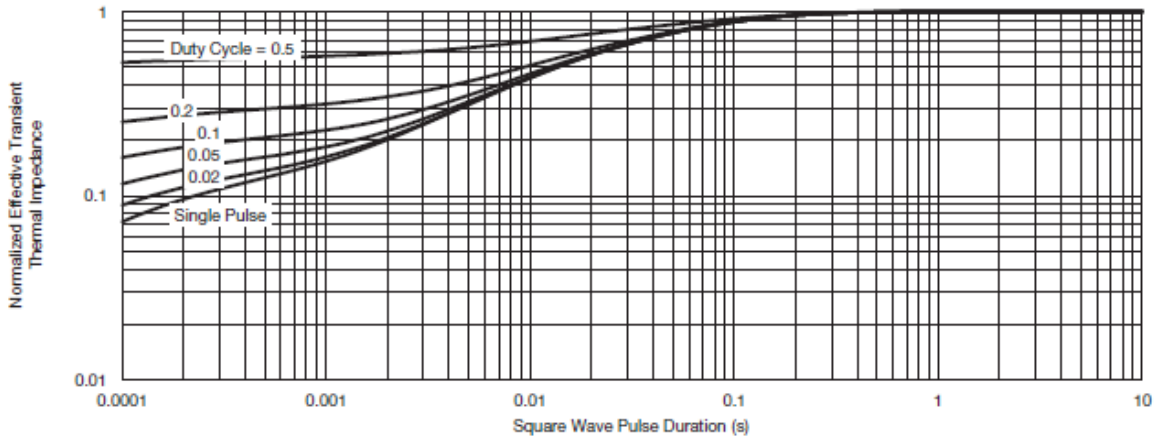
Power, Junction-to-Case



Power, Junction-to-Ambient



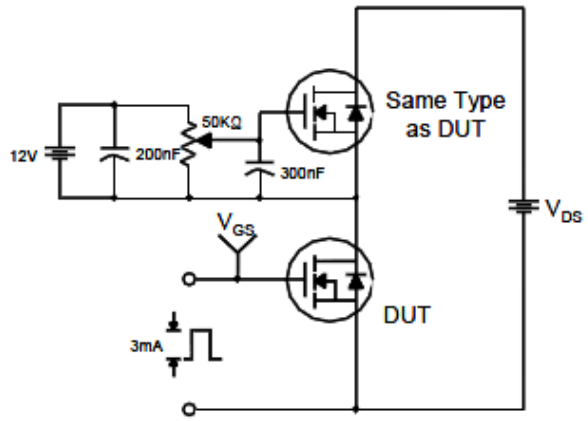
Normalized Thermal Transient Impedance, Junction-to-Ambient

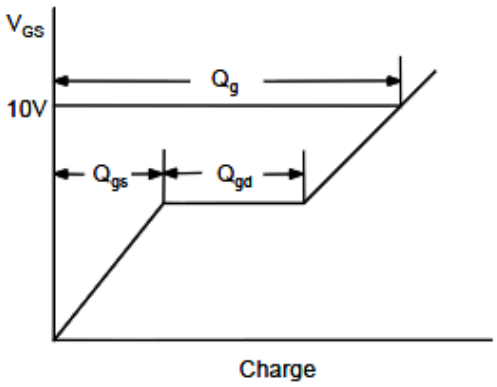


Normalized Thermal Transient Impedance, Junction-to-Case

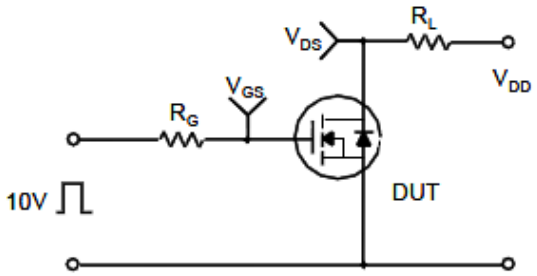
Typical Characteristics

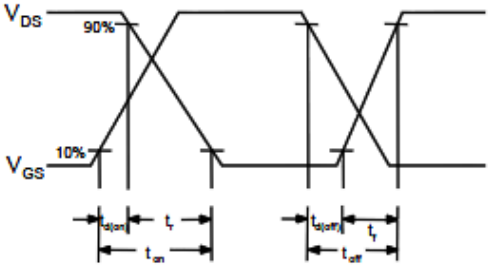
Gate Charge Test Circuit & Waveform



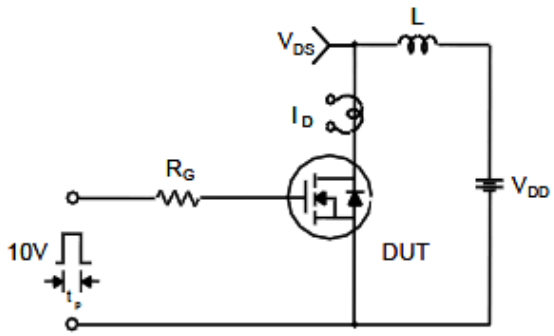


Resistive Switching Test Circuit & Waveforms

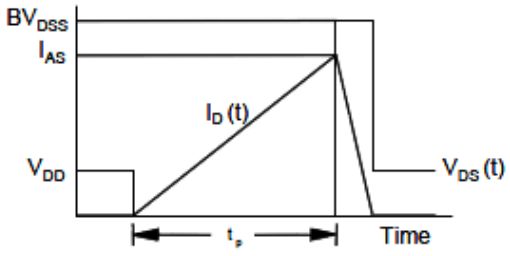




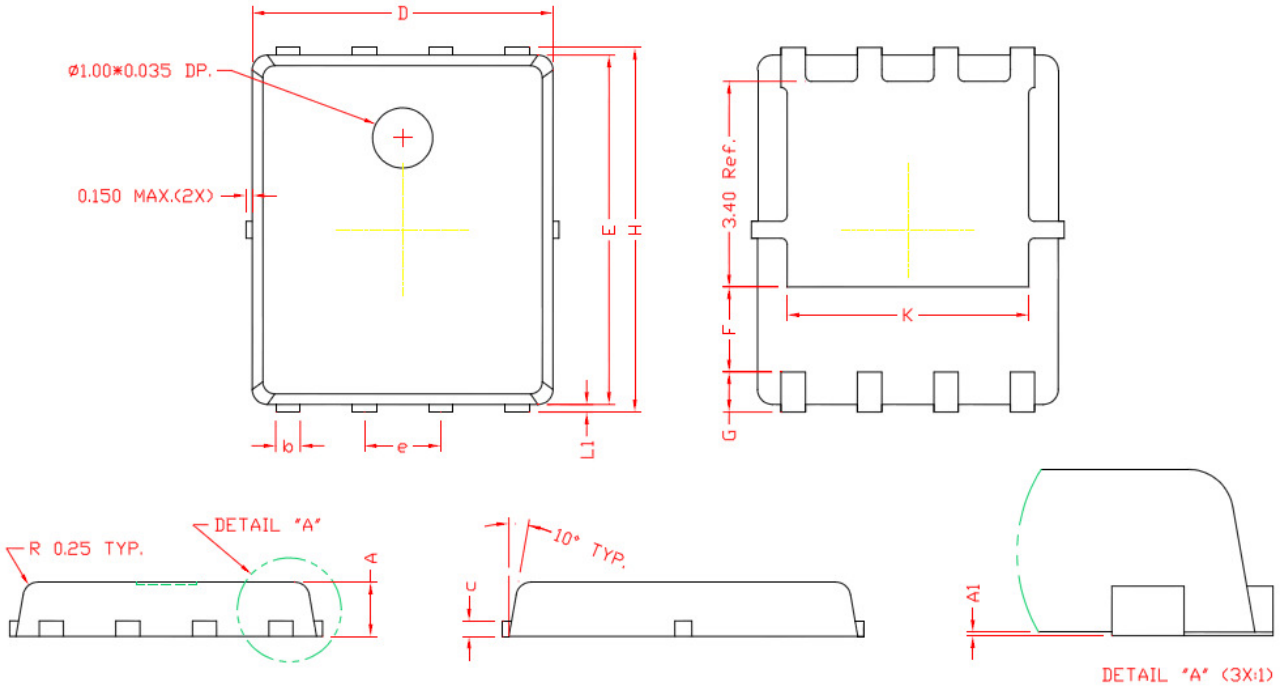
Unclamped Inductive Switching Test Circuit & Waveforms



$$E_{AS} = \frac{1}{2} L I_{AS}^2 \frac{BV_{DSS}}{BV_{DSS} - V_{DD}}$$



Package Information (DFN5X6-8L)



DIMENSIONS

REF.	Millimeters		REF.	Millimeters	
	Min.	Max.		Min.	Max.
A	0.80	1.00	E	5.70	5.90
A1	0.00	0.05	e	1.27 BSC.	
b	0.35	0.49	H	5.95	6.20
c	0.254 Ref.		L1	0.10	0.18
D	4.90	5.10	G	0.60 Ref.	
F	1.40 Ref.		K	4.00 Ref.	

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